

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	747	(327/427).CCLS.	US-PGPUB; USPAT
2	IS&R	L2	1	("20040164785").PN.	US-PGPUB; USPAT
3	IS&R	L3	188	(327/389).CCLS.	US-PGPUB; USPAT
4	IS&R	L4	239	(327/390).CCLS.	US-PGPUB; USPAT
5	IS&R	L5	173	(327/391).CCLS.	US-PGPUB; USPAT
6	IS&R	L6	1122	(307/112).CCLS.	US-PGPUB; USPAT
7	BRS	L7	79	6 and capacitor and diode	US-PGPUB; USPAT
8	BRS	L8	798	transistor near2 capacitor near2 diode	US-PGPUB; USPAT
9	BRS	L9	634	transistor near2 capacitor near2 diode	USOCR; EPO; JPO; DERWENT; IBM TDB
10	IS&R	L10	460	(327/434).CCLS.	US-PGPUB; USPAT
11	BRS	L11	170	10 and (diode and capacitor)	US-PGPUB; USPAT
12	BRS	L13	43	327/313.ccls. and (diode and capacitor)	US-PGPUB; USPAT
13	IS&R	L14	1	("5347231").PN.	US-PGPUB; USPAT
14	IS&R	L15	8	((("5734563") or ("5825079") or ("6038148") or ("6297970") or ("6420757") or ("6433370") or ("6537921") or ("6580150"))).PN.	US-PGPUB; USPAT
15	IS&R	L16	1	("20040135616").PN.	US-PGPUB; USPAT
16	IS&R	L19	70	(327/430).CCLS.	US-PGPUB; USPAT
17	IS&R	L20	1	("6208191").PN.	US-PGPUB; USPAT
18	BRS	L21	7	("4423431" "4533846" "5206544" "5301081" "5528190" "5534811" "5574395").PN.	US-PGPUB; USPAT; USOCR
19	IS&R	L22	3911	(327/309-333).CCLS.	US-PGPUB; USPAT
20	BRS	L24	733	22 and transistor and diode and capacitor	US-PGPUB; USPAT
21	BRS	L25	699	24 not (1 3 4 5 6 8)	US-PGPUB; USPAT
22	BRS	L26	2308	transistor with capacitor with diode.clm.	US-PGPUB; USPAT
23	BRS	L27	2013	transistor near3 capacitor near3 diode	US-PGPUB; USPAT
24	BRS	L28	345	27.clm.	US-PGPUB; USPAT
25	BRS	L29	193	28 not 8	US-PGPUB; USPAT

26	BRS	L30	389	1 and capacitor	US-PGPUB; USPAT
27	BRS	L31	22	("5563545").URPN.	USPAT

	Type	L #	Hits	Search Text	DBs
28	BRS	L32	2	("5115143").URPN.	USPAT
29	BRS	L33	5450	(transistor MOS fet).ti. and capacitor and diode	USOCR; EPO; JPO; DERWENT; IBM_TDB
30	BRS	L34	2392	(transistor MOS fet).ti. and capacitor near4 diode	USOCR; EPO; JPO; DERWENT; IBM_TDB
31	BRS	L35	1983	(transistor MOS fet).ti. and capacitor near3 diode	USOCR; EPO; JPO; DERWENT; IBM_TDB
32	BRS	L36	1768	35 not 9	USOCR; EPO; JPO; DERWENT; IBM_TDB
33	BRS	L37	115	36 and drain	USOCR; EPO; JPO; DERWENT; IBM_TDB
34	IS&R	L38	227	(327/493).CCLS.	US-PGPUB; USPAT
35	IS&R	L39	70	(327/430).CCLS.	US-PGPUB; USPAT
36	BRS	L42	23	((three two) adj terminal\$1).ti. and capacitor near3 diode	USOCR; EPO; JPO; DERWENT; IBM_TDB
37	BRS	L43	2	(transistor MOS fet) adj2 simulat\$3.ti. and capacitor near3 diode	USOCR; EPO; JPO; DERWENT; IBM_TDB
38	BRS	L44	46	(transistor MOS fet) adj2 simulat\$3.ti.	USOCR; EPO; JPO; DERWENT; IBM_TDB
39	IS&R	L45	0	(713/14).CCLS.	US-PGPUB; USPAT
40	IS&R	L46	717	(703/14).CCLS.	US-PGPUB; USPAT
41	BRS	L47	27	46 and transistor and capacitor and diode	US-PGPUB; USPAT
42	BRS	L48	1475	transistor near3 capacitor near3 diode	USOCR; EPO; JPO; DERWENT; IBM_TDB
43	BRS	L49	841	48 not 9	USOCR; EPO; JPO; DERWENT; IBM_TDB